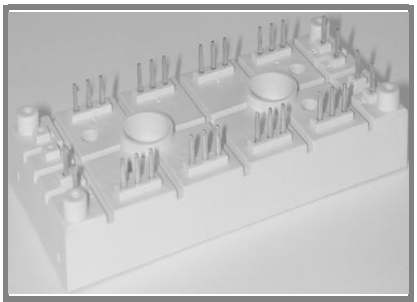
SKD 116/..L105



SEMIPONT™ 6

3-Phase Bridge Rectifier + IGBT braking chopper

SKD 116/..L105

Data

Features

- Compact design
- Two screws mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- High surge currents
- Up to 1600V reverse voltage
- IGBT Trench4 inside; max T_j=175°C
- CAL4F inside, max Tj=175°C
- I_{CM}/I_{FM} = 3x$I_{C,nom}/I_{F,nom}$
- Rectifier diode, max Tj=150°C

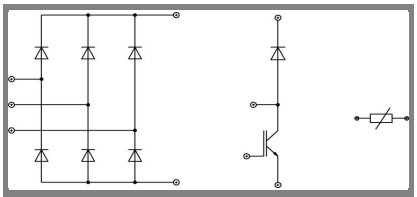
Typical Applications*

- DC drives
- Controlled filed rectifiers for DC motors
- Controlled battery charger

V_{RSM} V	V_{RRM}, V_{DRM} V	I_D = 110 A (maximum value for continuous operation) (T_s = 85 °C)
1300	1200	SKD 116/12-L105
1700	1600	SKD 116/16-L105

Absolute Maximum Ratings		T_s = 25 °C, unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
Bridge - Rectifier			
I_D	T_s = 85 °C; inductive load	110	A
I_{FSM}/I_{TSM}	t_p = 10 ms; sin 180° ; T_{jmax}	1050	A
i^2t	t_p = 10 ms; sin 180° ; T_{jmax}	5500	A²s
IGBT - Chopper			
V_{CES}/V_{GES}		1200 / 20	V
I_C	T_s = 25 (70) °C	123 (100)	A
I_{CM}	t_p = 1 ms; T_s = 25 (70) °C	315	A
Freewheeling - CAL Diode			
V_{RRM}		1200	V
I_F	T_s = 25 (70) °C	90 (75)	A
I_{FM}	t_p = 1 ms; T_s = 25 (70) °C	300	A
T_{vj}	Diode & IGBT (Thyristor)	- 40 ... + 175 (-40...+ 125)	°C
T_{stg}		- 40 ... + 125	°C
T_{solder}	terminals, 10 s	260	°C
V_{isol}	a.c. (50) Hz, RMS 1 min. / 1 s	3000 / 3600	V

Characteristics		T_s = 25 °C, unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
Diode - Rectifier					
V_{TO} / r_t	T_j = 125 °C		0,8 / 7		V / mΩ
$R_{th(j-s)}$	per diode			1	K/W
IGBT - Chopper					
$V_{CE(sat)}$	I_C = 105 A, T_j = 25 °C; V_{GE} = 15 V		1,85	2,1	V
$R_{th(j-s)}$	per IGBT		0,46		K/W
$t_{d(on)}$ / t_r	valid for all values:		97 / 185		ns
$t_{d(off)}$ / t_f	V_{CC} = 600 V; V_{GE} = 15 V; I_C = 105 A; T_j = 150 °C;		443 / 82		ns
$E_{on}+E_{off}$	T_j = 150 °C; R_G = 3 Ω; inductive load		47,5		mJ
CAL - Diode - Freewheeling					
$V_{T(TO)}$ / r_t	T_j = 150 °C		0,9 / 12,5	1,1 / 13,7	V / mΩ
$R_{th(j-s)}$	per diode		0,75		K/W
I_{RRM}	valid for all values:		22		A
Q_{rr}	I_F = 105 A; V_R = - 600 V; dI_F/dt = - 1700 A/µs		7		µC
E_{off}	V_{GE} = 0 V; T_j = 150 °C		5,94		mJ
Temperature Sensor					
R_{TS}	T = 25 (100) °C;		1000 (1670)		Ω
Mechanical data					
M_S	mounting Torque	2,55		3,45	Nm



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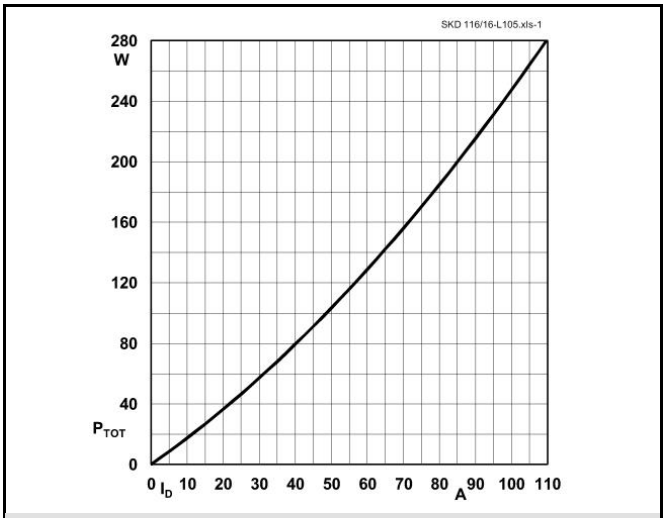

Fig. 1 Power dissipation per module vs. output current

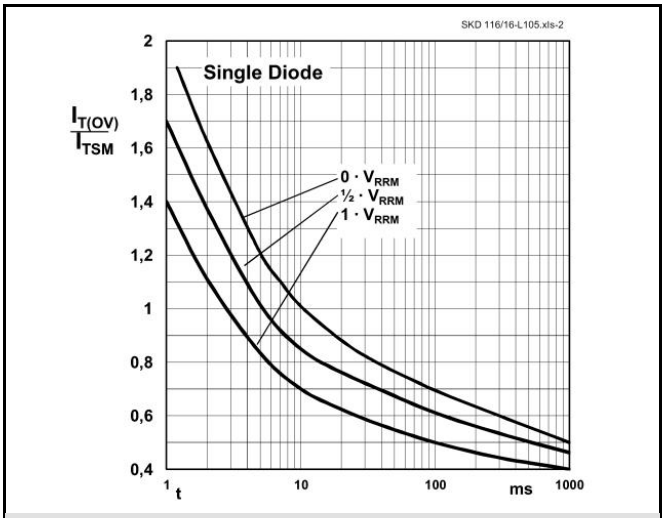

Fig. 2 Surge overload current vs. time

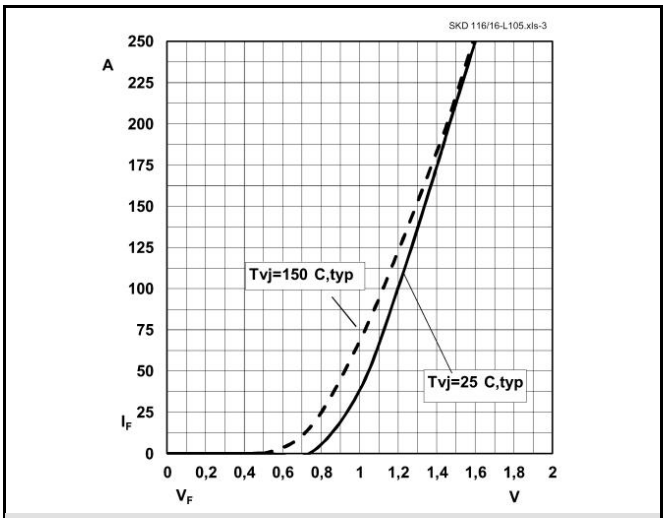

Fig. 3 Forward characteristic of single rectifier diode

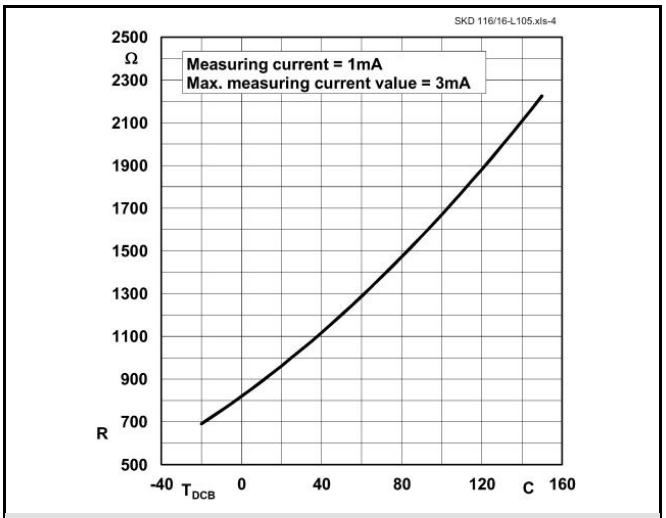

Fig. 4 Temperature sensor characteristic

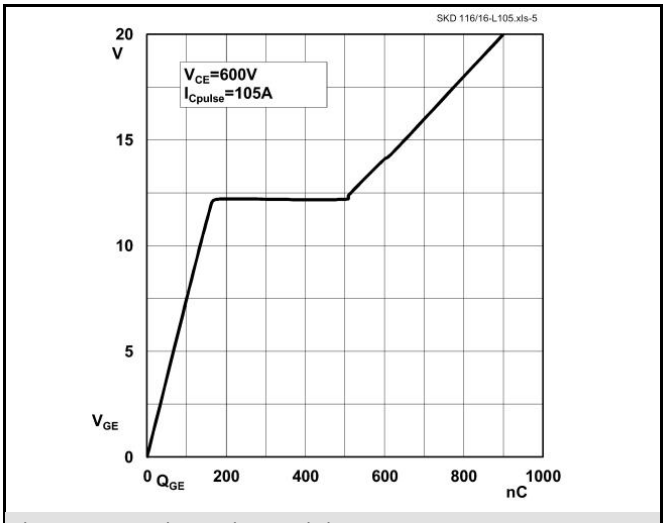

Fig. 5 Typ. gate charge characteristic

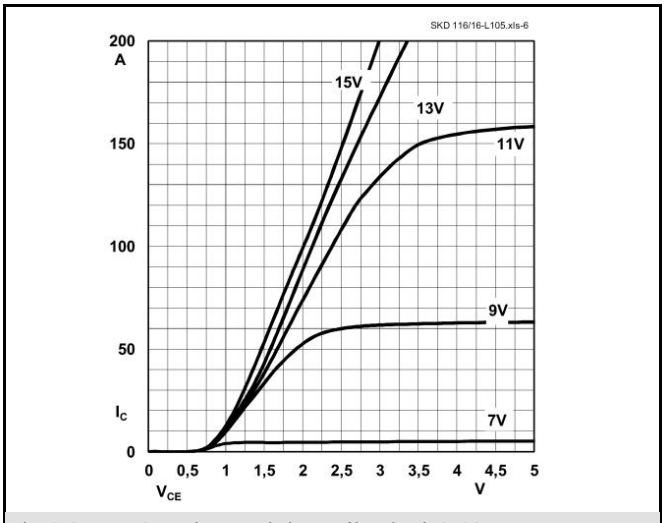

Fig. 6 Output IGBT characteristics Ic=f(Vce), Tj=25°C

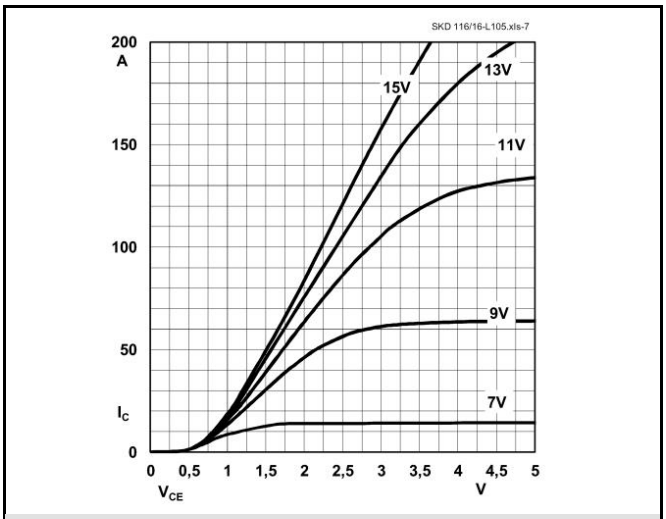

Fig. 7 Output IGBT characteristics Ic=f(Vce), Tj=125°C

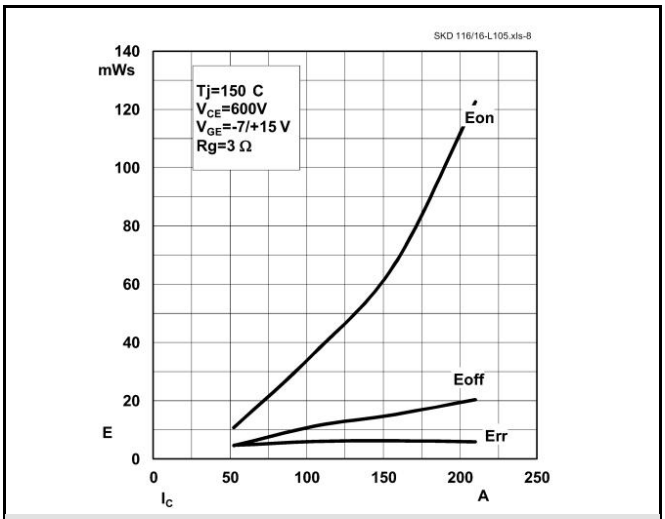

Fig. 8 Turn-on/-off energy=f(Ic)

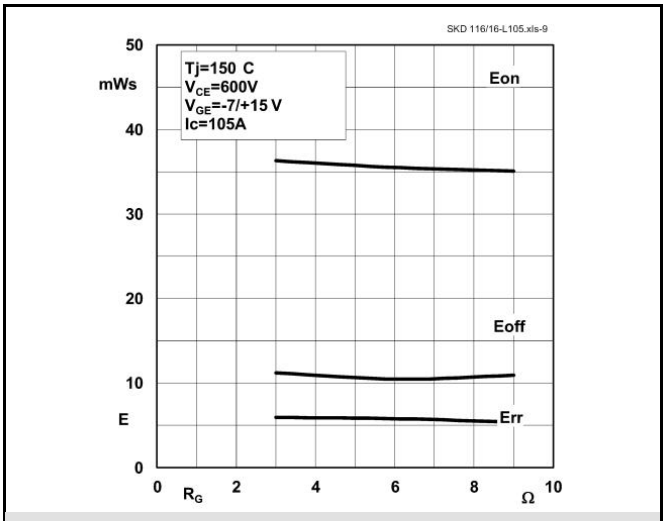

Fig. 9 Turn-on/-off energy=f(Rg)

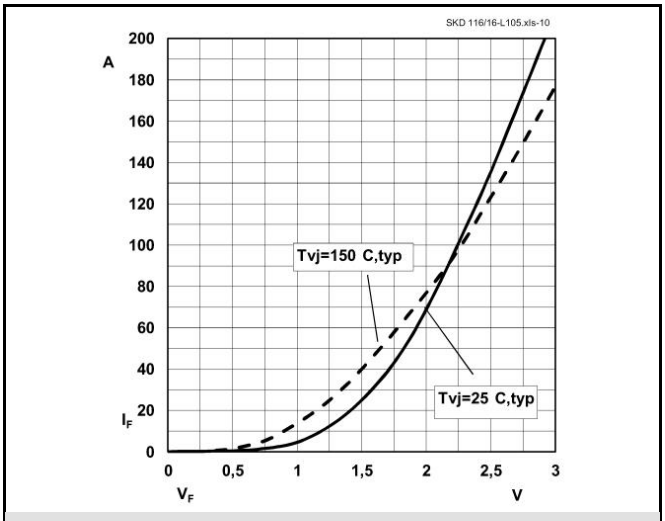

Fig. 10 Diode forward characteristic

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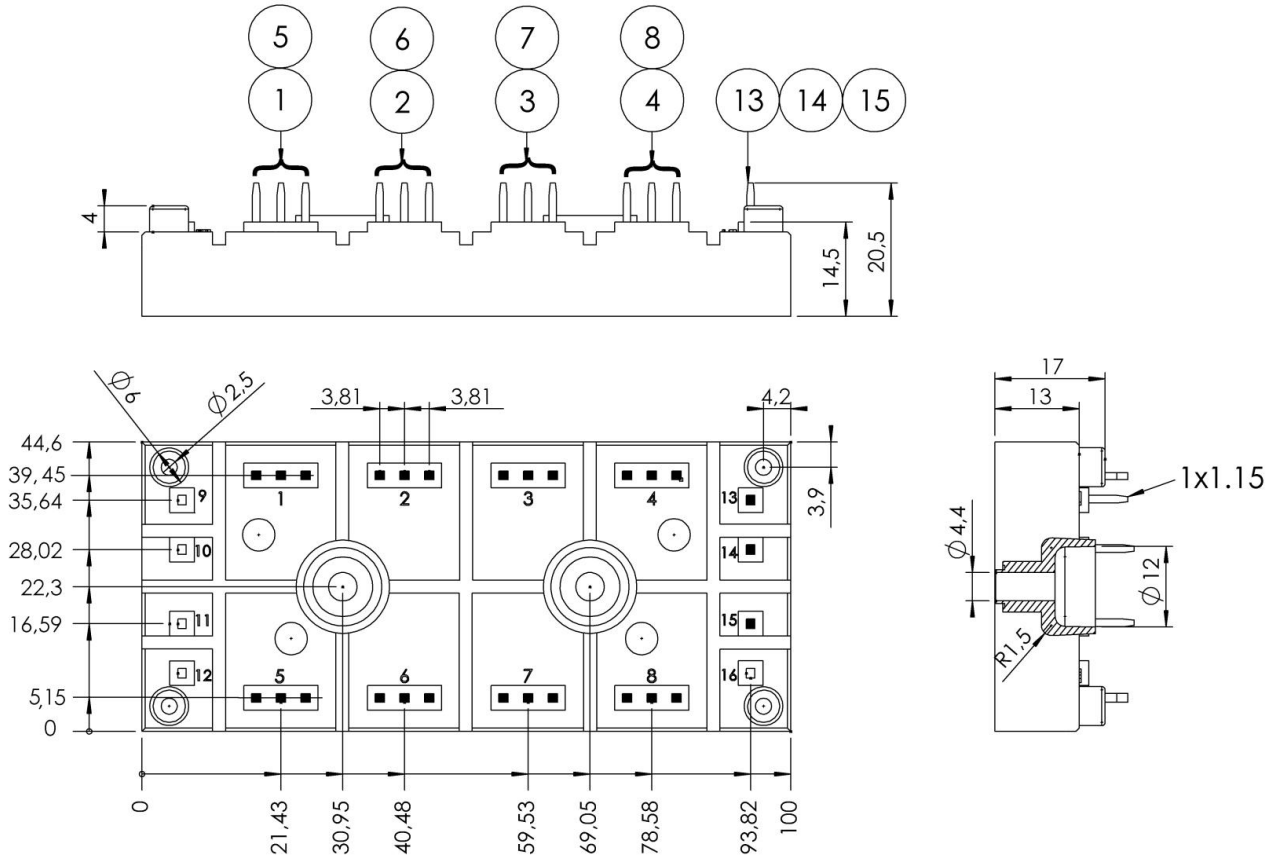
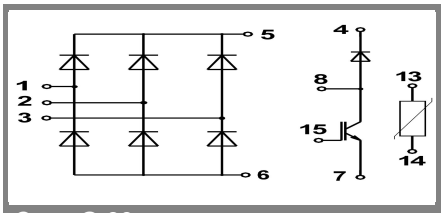
UL recognized
file no. E 63 532

Dimensions in mm



Case G 60



Case G 60

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.

